

SIDACtor Device



DO-214AA *SIDACtor* solid state protection devices protect telecommunications equipment such as modems, line cards, fax machines, and other CPE.

SIDACtor devices are used to enable equipment to meet various regulatory requirements including GR 1089, ITU K.20, K.21 and K.45, IEC 60950, UL 60950, and TIA/EIA-IS-968 (formerly known as FCC Part 68).

Electrical Parameters

| Part Number * | V _{DRM} Volts | V _S Volts | V _T Volts | I _{DRM} μ Amps | I _S mAmps | I _T Amps | I _H mAmps | C _O pF |
|---------------|------------------------|----------------------|----------------------|-----------------------------|----------------------|---------------------|----------------------|-------------------|
| P0080S_ | 6 | 25 | 4 | 5 | 800 | 2.2 | 50 | 100 |
| P0300S_ | 25 | 40 | 4 | 5 | 800 | 2.2 | 50 | 110 |
| P0640S_ | 58 | 77 | 4 | 5 | 800 | 2.2 | 150 | 50 |
| P0720S_ | 65 | 88 | 4 | 5 | 800 | 2.2 | 150 | 50 |
| P0900S_ | 75 | 98 | 4 | 5 | 800 | 2.2 | 150 | 50 |
| P1100S_ | 90 | 130 | 4 | 5 | 800 | 2.2 | 150 | 40 |
| P1300S_ | 120 | 160 | 4 | 5 | 800 | 2.2 | 150 | 40 |
| P1500S_ | 140 | 180 | 4 | 5 | 800 | 2.2 | 150 | 40 |
| P1800S_ | 170 | 220 | 4 | 5 | 800 | 2.2 | 150 | 30 |
| P2300S_ | 190 | 260 | 4 | 5 | 800 | 2.2 | 150 | 30 |
| P2600S_ | 220 | 300 | 4 | 5 | 800 | 2.2 | 150 | 30 |
| P3100S_ | 275 | 350 | 4 | 5 | 800 | 2.2 | 150 | 30 |
| P3500S_ | 320 | 400 | 4 | 5 | 800 | 2.2 | 150 | 30 |

* For individual "SA", "SB", and "SC" surge ratings, see table below.

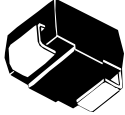
General Notes:

- All measurements are made at an ambient temperature of 25 °C. I_{PP} applies to -40 °C through +85 °C temperature range.
- I_{PP} is a repetitive surge rating and is guaranteed for the life of the product.
- Listed *SIDACtor* devices are bi-directional. All electrical parameters and surge ratings apply to forward and reverse polarities.
- V_{DRM} is measured at I_{DRM}.
- V_S is measured at 100 V/ μ s.
- Special voltage (V_S and V_{DRM}) and holding current (I_H) requirements are available upon request.
- Off-state capacitance is measured at 1 MHz with a 2 V bias and is a typical value for "SA" and "SB" product. "SC" capacitance is approximately 2x the listed value. The off-state capacitance of the P0080SB is equal to the "SC" device.

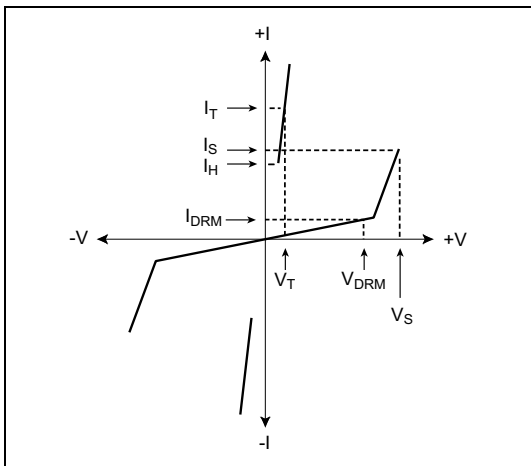
Surge Ratings

| Series | I _{PP} 2x10 μ s Amps | I _{PP} 8x20 μ s Amps | I _{PP} 10x160 μ s Amps | I _{PP} 10x560 μ s Amps | I _{PP} 10x1000 μ s Amps | I _{TSM} 60 Hz Amps | di/dt Amps/ μ s |
|--------|-----------------------------------|-----------------------------------|-------------------------------------|-------------------------------------|--------------------------------------|-----------------------------|---------------------|
| A | 150 | 150 | 90 | 50 | 45 | 20 | 500 |
| B | 250 | 250 | 150 | 100 | 80 | 30 | 500 |
| C | 500 | 400 | 200 | 150 | 100 | 50 | 500 |

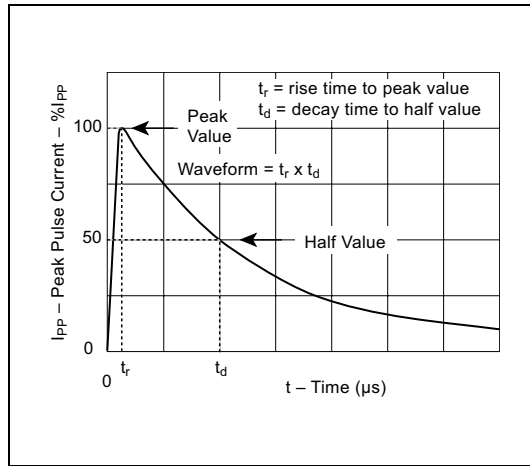
Thermal Considerations

| Package | Symbol | Parameter | Value | Unit |
|---|-----------------|---|-------------|-----------------------------|
|  | T_J | Operating Junction Temperature Range | -40 to +150 | $^{\circ}\text{C}$ |
| | T_S | Storage Temperature Range | -65 to +150 | $^{\circ}\text{C}$ |
| | $R_{\theta JA}$ | Thermal Resistance: Junction to Ambient | 90 | $^{\circ}\text{C}/\text{W}$ |

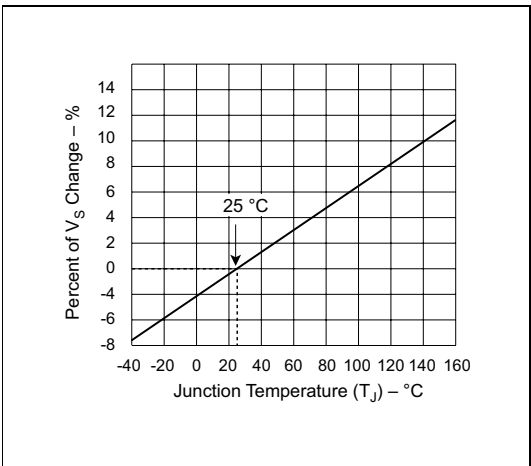
Data Sheets



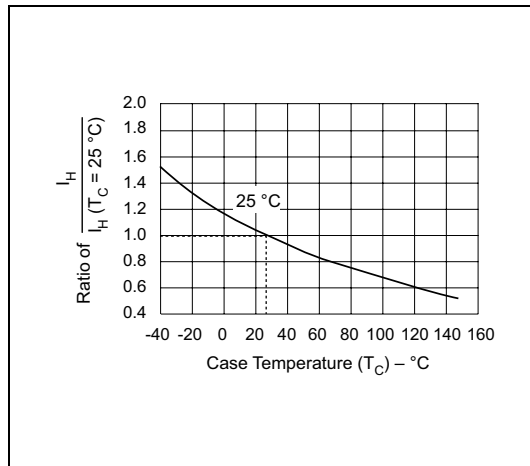
V-I Characteristics



$t_r \times t_d$ Pulse Wave-form



Normalized V_S Change versus Junction Temperature



Normalized DC Holding Current versus Case Temperature